

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	59419	MOSFET or (metal adj oxide adj semiconductor adj field adj effect adj transistor)	USPAT; US-PGP; UB; EPO; JPO; DERVENT; IBM_TDB	2002/09/25 12:15			0
2	BRS	L15	47473	1 and (insulat\$4 or oxide or gate)	USPAT; US-PGP; UB; EPO; JPO; DERVENT; IBM_TDB	2002/09/25 12:19			0
3	BRS	L22	4712	15 and (trench\$3)	USPAT; US-PGP; UB; EPO; JPO; DERVENT; IBM_TDB	2002/09/25 12:23			0
4	BRS	L29	2493	22 and ((silicon adj1 oxide) or (silicon adj1 nitride))	USPAT; US-PGP; UB; EPO; JPO; DERVENT; IBM_TDB	2002/09/25 12:25			0
5	BRS	L36	2407	29 and (first or second)	USPAT; US-PGP; UB; EPO; JPO; DERVENT; IBM_TDB	2002/09/25 12:28			0
6	BRS	L43	1806	36 and (temperature or heat or (1,100))	USPAT; US-PGP; UB; EPO; JPO; DERVENT; IBM_TDB	2002/09/25 12:30			0
7	BRS	L50	387	43 and ("Si.sub.3 N.sub.4")	USPAT; US-PGP; UB; EPO; JPO; DERVENT; IBM_TDB	2002/09/25 12:31			0
8	BRS	L64	119	50 and (angstroms)	USPAT; US-PGP; UB; EPO; JPO; DERVENT; IBM_TDB	2002/09/25 12:33			0
9	BRS	L71	119	64 and (thickness or LPCVD or (low adj1 pressure adj1 chemical adj1 vapor adj1 deposition))	USPAT; US-PGP; UB; EPO; JPO; DERVENT; IBM_TDB	2002/09/25 13:08			0